

APPENDIX VI

STATUTORY AND GENERAL INFORMATION

A. FURTHER INFORMATION ABOUT OUR GROUP

1. Incorporation of Our Company

Our Company was established as a limited liability company under the laws of the PRC on December 4, 2012, and was converted into a joint stock company with limited liability on June 28, 2022. We were registered with the Registrar of Companies in Hong Kong as a non-Hong Kong company under Part 16 of the Companies Ordinance on December 24, 2025, and have established a place of business in Hong Kong at 40/F, Dah Sing Financial Centre, No. 248 Queen’s Road East, Wanchai, Hong Kong. Ms. Yung Mei Yee has been appointed as the authorized representative of our Company for the acceptance of service of process and notices in Hong Kong.

As our Company was established in the PRC, our operations are subject to the relevant laws and regulations of the PRC. A summary of relevant aspects of PRC law and our Articles of Association is set out in “Taxation and Foreign Exchange,” “Summary of Principal Legal and Regulatory Provisions” and “Summary of Articles of Association” in Appendices III, IV and V to this document.

2. Changes in the Share Capital of Our Company

Save as disclosed in “History, Development and Corporate Structure,” there has been no alteration in the share capital of the Company within two years immediately preceding the date of this document.

3. Changes in the Share Capital of Our Subsidiaries

A summary of the corporate information and the particulars of our principal subsidiaries are set out in Note 1 to the Accountants’ Report in Appendix I to this document.

The following subsidiaries of our Company were established within two years immediately preceding the date of this document:

<u>Name of subsidiary</u>	<u>Place of incorporation</u>	<u>Date of incorporation</u>	<u>Registered capital</u>
Hengqin Tuowei	PRC	February 28, 2025	RMB5,000,000
Vergiga Zhoushan	PRC	September 4, 2025	RMB80,000,000

There has been no alteration in the share capital of our subsidiaries within the two years immediately preceding the date of this document.

4. Resolutions of Our Shareholders

On December 12, 2025, resolutions of our Shareholders were passed pursuant to which, among other things:

- (a) subject to the completion of the [REDACTED], the Articles was approved and adopted with effect from the [REDACTED];

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- (b) the [REDACTED] (including the [REDACTED], [REDACTED] and [REDACTED]) and the [REDACTED] were approved and our Directors were authorized to allot and issue the [REDACTED] pursuant to the [REDACTED];
- (c) the number of H Shares to be [REDACTED] shall be up to [REDACTED]% of the total share capital of our Company upon completion of the [REDACTED] and before any exercise of the [REDACTED], and the grant of the [REDACTED] in respect of no more than [REDACTED]% of the number of H Shares initially issued pursuant to the [REDACTED];
- (d) subject to the completion of the [REDACTED], the granting of a general mandate to the Board to allot and issue Shares at any time within a period up to the date of the conclusion of the next annual general meeting of the Shareholders after the [REDACTED] or the date on which the Shareholders pass a special resolution to revoke or change such mandate, whichever is earlier, upon such terms and conditions and for such purposes and to such persons as the Board in their absolute discretion deem fit, and to make necessary amendments to the Articles of Association, provided that, the number of Shares to be issued shall not exceed 20% of the number of the Shares in issue as at the date of the resolution granting the general mandate; and
- (e) subject to the filing procedure with the CSRC, upon completion of the [REDACTED], [REDACTED] Unlisted Shares will be converted into H Shares on a one-on-one basis.

B. FURTHER INFORMATION ABOUT OUR BUSINESS

1. Summary of Material Contracts

The following contracts (not being contracts entered into in the ordinary course of the business carried on or intended to be carried on by our Company) were entered into by any member of our Group within the two years preceding the date of this document and are or may be material:

- (a) [●]; and
- (b) the [REDACTED].

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2. Our Intellectual Property Rights

(a) Trademarks

As of the Latest Practicable Date, we had registered the following trademarks which we consider to be material in relation to our business:

No.	Trademark	Class	Registrant	Place of registration	Registration number	Expiry date
1 . . .		9	The Company	PRC	16841041	June 27, 2036
2 . . .	威兆	9	The Company	PRC	52970332	November 27, 2031
3 . . .	威兆	42	The Company	PRC	56433072	February 6, 2032
4 . . .	vergiga	9	The Company	PRC	62152994	July 6, 2032
5 . . .	vergiga	42	The Company	PRC	62159188	July 13, 2032
6 . . .		9	The Company	PRC	62169758	August 27, 2033
7 . . .		9	The Company	PRC	62152965	October 27, 2032
8 . . .		9	The Company	Taiwan	02195734	January 15, 2032
9 . . .		9	The Company	Singapore	40202113542Y	June 8, 2031
10 . .		9	The Company	India	5000273	June 10, 2031
11 . .		9	The Company	Hong Kong	305654999	June 10, 2031
12 . .		9	The Company	Malaysia	TM2021016203	June 9, 2031
13 . .		9	The Company	Japan	6532292	March 23, 2032
14 . .		9	The Company	Korea	40-2018-0097034	April 11, 2029

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(b) Patents

As of the Latest Practicable Date, we had registered the following patents which we consider to be material to our business:

No.	Patent	Patent type	Patentee	Patent number	Expiry date
1 . . .	A Terminal Structure, Semiconductor Device and its Manufacturing Method (一種終端結構、半導體器件及製作方法)	Invention Patent	Zhuhai Vergiga	ZL202110651512.4	June 9, 2041
2 . . .	A Terminal Structure, Semiconductor Device and its Manufacturing Method (一種終端結構、半導體器件及製作方法)	Invention Patent	Zhuhai Vergiga	ZL202110651513.9	June 9, 2041
3 . . .	Buried Layer Terminal Structure and its Preparation Method (埋層終端結構及其制備方法)	Invention Patent	Zhuhai Haochen	ZL202110695201.8	June 21, 2041
4 . . .	Composite Layer Terminal Structure and its Preparation Method (複合終端結構及其制備方法)	Invention Patent	Zhuhai Haochen	ZL202110695000.8	June 21, 2041
5 . . .	Ultra-junction MOSFET Devices and Chips (超結 MOSFET器件及芯片)	Invention Patent	The Company	ZL202110554780.4	May 19, 2041
6 . . .	A Voltage Sampling Structure Based on SGT-MOSFETs (一種基於SGT-MOSFET的電壓採樣結構)	Invention Patent	The Company	ZL202210048704.0	January 16, 2042
7 . . .	A Integrated SGT-MOSFET Device for Voltage Sampling (一種集成式電壓採樣的SGT-MOSFET器件)	Invention Patent	The Company	ZL202210048703.6	January 16, 2042

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No.	Patent	Patent type	Patentee	Patent number	Expiry date
8 . . .	Cell Structure, Transistor, and Manufacturing Method of Shielded Gate Metal Oxide Semiconductor Field Effect Transistor (屏蔽柵極金氧半場效晶體管元胞結構、晶體管及製造方法)	Invention Patent	The Company	ZL202210049709.5	January 16, 2042
9 . . .	A IGBT Device and its Manufacturing Method (一種IGBT器件及其製造方法)	Invention Patent	The Company	ZL202210062869.3	January 19, 2042
10 . .	A Shielded Gate Device Featuring Temperature Sampling (一種帶溫度採樣功能的屏蔽柵器件)	Invention Patent	The Company	ZL202210403811.0	April 17, 2042
11 . .	A Semiconductor Device, Terminal Structure and its Manufacturing Method (一種半導體器件、終端結構及其製造方法)	Invention Patent	The Company	ZL202210227409.1	March 9, 2042
12 . .	A IGBT Device and its Manufacturing Method (一種IGBT器件及其製造方法)	Invention Patent	The Company	ZL202210327695.9	March 30, 2042
13 . .	Trench Gate Ultra-junction VOMOS Devices, Chips, and Terminal Equipment (槽柵超結VDMOS器件、芯片及終端設備)	Invention Patent	The Company	ZL202110581224.6	May 25, 2041
14 . .	A Simulation Method of Ultra-junction MOSFET Device (一種超結MOSFET器件的仿真方法)	Invention Patent	The Company	ZL202210485117.8	May 5, 2042
15 . .	A SiC MOS Device Featuring Enhanced Short-Circuit Performance (一種改善短路特性的碳化硅MOS器件)	Invention Patent	The Company	ZL202210502977.8	May 9, 2042

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16 . .	A Dual-channel MOSFET Device and its Manufacturing Method (一種雙溝道MOSFET器件及其製造方法)	Invention Patent	The Company	ZL202210631851.0	June 6, 2042
17 . .	A Conduction Voltage Drop Self-Clamping Semiconductor Device and its Manufacturing Method (一種具有導通壓降自鉗位的半導體器件及其製造方法)	Invention Patent	The Company	ZL202210777870.4	July 3, 2042
18 . .	A Staged Trench Gate SiC MOSFET Structure with Channel Diode and its Preparation Method (一種具有溝道二極管的階梯溝槽柵SiC MOSFET結構及其制備方法)	Invention Patent	The Company	ZL202210876258.2	July 24, 2042
19 . .	A Trench Gate SiC MOSFET Device with Dual-channel Diode and its Preparation Method (一種具有雙溝道二極管的溝槽柵SiC MOSFET器件及其制備方法)	Invention Patent	The Company	ZL202210876407.5	July 24, 2042
20 . .	A Novel Ultra-junction VDMOS Structure and its Preparation Method (一種超結VDMOS新結構及其制備方法)	Invention Patent	The Company	ZL202211078330.3	September 4, 2042
21 . .	Preparation Method of Ultra-junction MOSFETs (一種超結MOSFET的制備方法)	Invention Patent	The Company	ZL202110574914.9	May 24, 2041
22 . .	A Ultra-junction MOSFET (一種超結MOSFET)	Invention Patent	The Company	ZL202211077819.9	September 4, 2042

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23 . .	A Thermal Dissipation Device and Thermal Dissipation Methods of Variable Frequency Drive MOSFETs (一種變頻器 MOSFET的散熱裝置及散熱方法)	Invention Patent	The Company	ZL202210973299.3	August 14, 2042
24 . .	A Shielded Gate MOSFET and Manufacturing Method (一種屏蔽柵MOSFET及製作方法)	Invention Patent	The Company	ZL202111025942.1	September 1, 2041
25 . .	A Fast Recovery Diode and its Preparation Method (一種快恢復二極管及其制備方法)	Invention Patent	The Company	ZL202211234158.6	October 9, 2042
26 . .	Fast Recovery Diode and its Preparation Methods (快恢復二極管及其制備方法)	Invention Patent	The Company	ZL202211233564.0	October 9, 2042
27 . .	A Method, Device and Medium for Cleaning and Drying MOSFET Trenches with Feedback (一種反饋式MOSFET溝槽的清洗乾燥方法、裝置及介質)	Invention Patent	The Company	ZL202211142961.7	September 19, 2042
28 . .	A Finite Element Modeling Method and System Based on High Temperature Characteristics of IGBT (一種基於IGBT高溫特性的有限元建模方法及系統)	Invention Patent	The Company	ZL202211194490.4	September 28, 2042

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29 . .	A Dynamic Simulation Method and System of IGBT Fault Operation Parameters (一種 IGBT故障運行參數的動態模擬方法及系統)	Invention Patent	The Company	ZL202211245103.5	October 11, 2042
30 . .	A Semiconductor Device and its Manufacturing Method (半導體器件及其製造方法)	Invention Patent	The Company	ZL202211498206.2	November 27, 2042
31 . .	Insulated Gate Bipolar Transistors (絕緣柵雙極型晶體管)	Invention Patent	The Company	ZL202211417218.8	November 13, 2042
32 . .	A Terminal Voltage Withstand Adjustment Method of Insulated Gate Bipolar Transistors (絕緣柵雙極型晶體管的終端耐壓調整方法)	Invention Patent	The Company	ZL202211481979.X	November 23, 2042
33 . .	Insulated Gate Bipolar Transistor (絕緣柵雙極型晶體管)	Invention Patent	The Company	ZL202211482984.2	November 23, 2042
34 . .	Manufacturing Method of Insulated Gate Bipolar Transistors and Insulated Gate Bipolar Transistor (絕緣柵雙極型晶體管的製作方法及絕緣柵雙極型晶體管)	Invention Patent	The Company	ZL202211070222.1	August 31, 2042
35 . .	A Insulated Gate Bipolar Transistor (一種絕緣柵雙極型晶體管)	Invention Patent	The Company	ZL202211029687.2	August 24, 2042
36 . .	High-voltage Silicon Carbide Power Device Terminal and its Manufacturing Method (高壓碳化硅功率器件終端及其製造方法)	Invention Patent	The Company	ZL202310047582.8	January 30, 2043

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37 . .	Semiconductor Devices (半導體器件)	Invention Patent	The Company	ZL202310075946.3	February 6, 2043
38 . .	Insulated Gate Bipolar Transistor and its Gate Voltage Control Method for Carrier Concentration (絕緣柵雙極型晶體管及其載流子濃度控制方法)	Invention Patent	The Company	ZL202310256833.3	March 16, 2043
39 . .	Semiconductor Devices (半導體器件)	Invention Patent	The Company	ZL202310534527.1	May 11, 2043
40 . .	Semiconductor Devices (半導體器件)	Invention Patent	The Company	ZL202310534526.7	May 11, 2043
41 . .	Semiconductor Device and its Manufacturing Method (半導體器件及其製造方法)	Invention Patent	The Company	ZL202310614487.1	May 28, 2043
42 . .	Silicon Carbide MOSFET Device and its Manufacturing Method (碳化硅 MOSFET 器件及其製造方法)	Invention Patent	The Company	ZL202310614471.0	May 28, 2043
43 . .	Silicon Carbide MOSFET Device with High UIS Capability and its Manufacturing Method (具有高 UIS 能力的碳化硅 MOSFET 器件及其製造方法)	Invention Patent	The Company	ZL202310614478.2	May 28, 2043
44 . .	Vertical Semiconductor Device and its Manufacturing Method (半導體縱向器件及其生產方法)	Invention Patent	The Company	ZL202111213211.X	October 17, 2041

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45 . .	A Vertical Semiconductor Device and its Manufacturing Method (一種半導體縱向器件及其生產方法)	Invention Patent	The Company	ZL202111213878.X	October 17, 2041
46 . .	Semiconductor Device and its Manufacturing Method (半導體器件及其製造方法)	Invention Patent	The Company	ZL202310844509.3	July 10, 2043
47 . .	Semiconductor Device and its Preparation Method (半導體器件及其制備方法)	Invention Patent	The Company	ZL202310844510.6	July 10, 2043
48 . .	Gallium Nitride Power Devices (A Gallium Nitride Power Device and its Preparation Method) (氮化鎵功率器件(一種氮化鎵功率器件及其制備方法))	Invention Patent	The Company	ZL202410065349.7	January 16, 2044
49 . .	Bidirectional Gallium Nitride Power Devices (A Bidirectional Gallium Nitride Power Device and its Preparation Method) (氮化鎵雙向功率器件(一種氮化鎵雙向功率器件及其制備方法))	Invention Patent	The Company	ZL202410065348.2	January 16, 2044
50 . .	A Shielded Gate Trench MOSFET Device and its Preparation Method (一種屏蔽柵溝槽型 MOSFET 器件及其制備方法)	Invention Patent	The Company	ZL202410391005.5	April 1, 2044
51 . .	An Anti-dv/dt SGT Device (一種抗 dv/dt 的 SGT 器件)	Invention Patent	The Company	ZL202011065162.5	September 29, 2040

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52 . .	Shielded Gate MOSFET with Uniformly Doped Channel and its Processing Technology (具有均勻摻雜溝道的屏蔽栅MOSFET器件及加工工藝)	Invention Patent	The Company	ZL202011219018.2	November 3, 2040
53 . .	SGT Device and its Preparation Method (SGT器件及其制備方法)	Invention Patent	The Company	ZL202410186179.8	February 19, 2044
54 . .	A Semiconductor Device with ESD Protection Structure and its Preparation Method (一種具有ESD保護結構的半導體器件及其制備方法)	Invention Patent	The Company	ZL202411439017.7	October 14, 2044
55 . .	A Trench Gate IGBT Device (一種溝槽栅IGBT器件)	Invention Patent	Zhuhai Haochen	ZL202010928662.0	September 6, 2040
56 . .	A Trench Gate IGBT Device with Floating Structure (一種具有浮空結構的溝槽栅IGBT器件)	Invention Patent	Zhuhai Haochen	ZL202110153581.2	February 3, 2041
57 . .	A Shielded Gate MOSFET Device with Integrated NPN Punch-Through Triode (一種集成NPN穿通三極管的屏蔽栅MOSFET器件)	Invention Patent	The Company	ZL202011197262.3	October 29, 2040
58 . .	A Trench Gate IGBT Device with Discrete Floating Structure and Trenches (一種浮空結構與溝槽分立的溝槽栅IGBT器件)	Invention Patent	Zhuhai Haochen	ZL202110153724.X	February 3, 2041

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59 . .	A Composite Trough Grid Power Device and its Processing Technology (一種複合溝槽分立柵功率器件及其加工工藝)	Invention Patent	The Company	ZL202011427090.4	December 8, 2040
60 . .	A Trench MOS Cell and Preparation Method Thereof (一種溝槽MOS單元及其製備方法)	Invention Patent	The Company	ZL201410536089.3	October 10, 2034
61 . .	A Semiconductor Device Structure (一種半導體器件結構)	Invention Patent	The Company	ZL201610606441.5	July 28, 2036
62 . .	PiN Diode Based on Lateral Multi-channel Structure and Preparation Method Thereof (基於橫向多溝道結構的PiN二極管及其製備方法)	Invention Patent	The Company	ZL201710310424.1	May 4, 2037
63 . .	A Design Method for a VDMOS Voltage Divider Loop with Vertical multiple PN junctions (一種縱向多重PN結的VDMOS分壓環的設計方法)	Invention Patent	The Company	ZL201811550606.7	December 17, 2038
64 . .	Method for Manufacturing Semiconductor Device (A Method for Manufacturing an Insulated Gate Bipolar Transistor) (半導體器件的製造方法(一種絕緣柵雙極型晶體管製作方法))	Invention Patent	The Company	ZL202211442458.3	November 16, 2042

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65 . .	Semiconductor Power Device and Preparation Method Thereof (A Structure of High-Density Power Device and Preparation Method Thereof) (半導體功率器件及其製備方法(一種高密度功率器件的結構及其製備方法))	Invention Patent	The Company	ZL202510743104.X	June 4, 2045
66 . .	Semiconductor Power Device and Preparation Method Thereof (A Shielded Gate Trench Transistor Device and Preparation Method Thereof) (半導體功率器件及其製備方法(一種屏蔽柵溝槽型晶體管器件及其製備方法))	Invention Patent	The Company	ZL202510858120.3	June 24, 2045
67 . .	Gallium Nitride Power Device and Preparation Method Thereof (A Gallium Nitride Power Device and Preparation Method Thereof) (氮化鎵功率器件及其製備方法(一種氮化鎵功率器件及其製備方法))	Invention Patent	The Company	ZL202510858848.6	June 24, 2045
68 . .	A Metal Layer of IGBT Chip Layout (一種IGBT芯片版圖金屬層)	Utility Model	Zhuhai Haochen	ZL202021820854.1	August 26, 2030
69 . .	A Trench Gate IGBT Device (一種溝槽柵IGBT器件)	Utility Model	Zhuhai Haochen	ZL202021934492.9	September 6, 2030
70 . .	A Terminal Structure and Semiconductor Device (一種終端結構及半導體器件)	Utility Model	Zhuhai Haochen	ZL202121305452.2	June 9, 2031

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71 . .	A Terminal Structure and Semiconductor Device (一種終端結構及半導體器件)	Utility Model	Zhuhai Haochen	ZL202121306194.X	June 9, 2031
72 . .	Composite Terminal Structure (複合終端結構)	Utility Model	Zhuhai Haochen	ZL202121395001.2	June 21, 2031
73 . .	Buried Layer Terminal Structure (埋層終端結構)	Utility Model	Zhuhai Haochen	ZL202121395102.X	June 21, 2031
74 . .	A Trench Gate IGBT Device with Floating Structure and Discrete Trenches (一種浮空結構與溝槽分立的溝槽柵IGBT器件)	Utility Model	Zhuhai Haochen	ZL202120354474.1	February 3, 2031
75 . .	A Trench Gate IGBT Device with Floating Structure (一種具有浮空結構的溝槽柵IGBT器件)	Utility Model	Zhuhai Haochen	ZL202120329605.0	February 3, 2031
76 . .	A Trench MOSFET Device with NPN Sandwich Gate Structure (一種NPN三明治柵結構的溝槽MOSFET器件)	Utility Model	The Company	ZL202022483133.2	October 29, 2030
77 . .	A Shielded Gate MOSFET Device with Uniformly Doped Channel (一種具有均勻摻雜溝道的屏蔽柵MOSFET器件)	Utility Model	The Company	ZL202022530296.1	November 3, 2030
78 . .	A dv/dt-resistant SGT Device (一種抗dv/dt的SGT器件)	Utility Model	The Company	ZL202022224120.3	September 29, 2030
79 . .	An EMI-resistant SGT Device (一種抗EMI的SGT器件)	Utility Model	The Company	ZL202022224211.7	September 29, 2030
80 . .	A Schottky Diode (一種肖特基二極管)	Utility Model	The Company	ZL201720653343.7	June 5, 2027
81 . .	A DMOS Cut-off Ring (一種DMOS截止環)	Utility Model	The Company	ZL201720648610.1	June 5, 2027

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82 . .	A Shielded Gate MOSFET Device with Integrated NPN Punch-through Triode (一種集成NPN穿通三極管的屏蔽柵MOSFET器件)	Utility Model	The Company	ZL202022485628.9	October 29, 2030
83 . .	An SGT MOSFET Device with Bidirectional ESD Protection (一種具有雙向ESD保護能力的SGT MOSFET器件)	Utility Model	The Company	ZL202022484962.2	October 29, 2030
84 . .	A Composite Trough Grid Power Device (一種複合溝槽分立柵功率器件)	Utility Model	The Company	ZL202022933544.7	December 8, 2030
85 . .	Trench Gate Ultra-junction VDMOS Devices and Chips (槽柵超結VDMOS器件及芯片)	Utility Model	The Company	ZL202121154194.2	May 25, 2031
86 . .	Ultra-junction MOSFET Devices (超結MOSFET器件)	Utility Model	The Company	ZL202121092565.9	May 19, 2031
87 . .	Ultra-junction MOSFETs (超結MOSFET)	Utility Model	The Company	ZL202121129551.X	May 24, 2031
88 . .	Semiconductor Devices (半導體器件)	Utility Model	The Company	ZL202121045231.6	May 13, 2031
89 . .	Ultra-junction MOSFET Termination (超結MOSFET終端)	Utility Model	The Company	ZL202121253482.3	June 3, 2031
90 . .	Ultra-junction Power MOSFETs (超結功率MOSFET)	Utility Model	The Company	ZL202120976676.X	May 7, 2031
91 . .	An SGT Device with a PSG Dielectric Protection Layer (一種具有PSG介質保護層的SGT器件)	Utility Model	The Company	ZL202023248067.7	December 27, 2030

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92 . .	An SGT Device with a Dielectric Protection Layer (一種具有介質保護層的SGT器件)	Utility Model	The Company	ZL202023234842.3	December 27, 2030
93 . .	A Shielded Gate MOSFET (一種屏蔽柵MOSFET)	Utility Model	The Company	ZL202122114620.6	September 1, 2031
94 . .	Shielded Gate MOSFET Devices and Chips (屏蔽柵MOSFET器件和芯片)	Utility Model	The Company	ZL202122093215.0	August 30, 2031
95 . .	Semiconductor Devices (半導體器件)	Utility Model	The Company	ZL202122511036.4	October 17, 2031
96 . .	A Semiconductor Device (一種半導體器件)	Utility Model	The Company	ZL202122511154.5	October 17, 2031
97 . .	Semiconductor Package Construction (半導體封裝結構)	Utility Model	The Company	ZL202223599497.2	December 28, 2032
98 . .	Semiconductor Package Construction (半導體封裝結構)	Utility Model	The Company	ZL202223599454.4	December 28, 2032
99 . .	High Voltage Diode (高壓二極管)	Utility Model	The Company	ZL202223483800.2	December 20, 2032
100 . .	Diode Device (二極管器件)	Utility Model	The Company	ZL202223524744.2	December 20, 2032
101 . .	Semiconductor Devices (半導體器件)	Utility Model	The Company	ZL202223423034.0	December 15, 2032
102 . .	Diode Device (二極管器件)	Utility Model	The Company	ZL202223489328.3	December 20, 2032
103 . .	Glass Cleaning Equipment (玻璃清潔設備)	Utility Model	Zhuhai Vergiga	ZL202422039053.6	August 20, 2034
104 . .	A High-Efficiency Heating Melt Adhesive Machine (Hot Melt Adhesive Machine Solution) (一種高效加熱解膠機(熱解膠機方案))	Utility Model	Zhuhai Vergiga	ZL202422672712.X	October 27, 2035

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No.	Patent	Patent type	Patentee	Patent number	Expiry date
105.	An Adjustable Wafer Fixture and Melt Adhesive Machine (Hot Melt Adhesive Machine Solution) (一種可調晶圓夾具及解膠機(熱解膠機方案))	Utility Model	Zhuhai Vergiga	ZL202422671145.6	October 31, 2034
106.	Glass Testing Equipment (玻璃檢測設備)	Utility Model	Zhuhai Vergiga	ZL202422083209.0	August 25, 2034
107.	Semiconductor Metal Cleaning Equipment (半導體金屬清洗設備)	Utility Model	Zhuhai Vergiga	ZL202422210936.9	September 8, 2034
108.	Semiconductor Metal Cleaning Equipment (半導體金屬清洗設備)	Utility Model	Zhuhai Vergiga	ZL202422292481.X	September 18, 2034
109.	Rotary Glass Ultrasonic Cleaning Device (旋轉式玻璃超聲波清潔設備)	Utility Model	Zhuhai Vergiga	ZL202422188192.5	September 4, 2034
110.	An Anti-splash Vapor Deposition Device (一種防飛濺的蒸鍍裝置)	Utility Model	Zhuhai Vergiga	ZL202520986725.6	May 18, 2035
111.	Integrated Wafer Detaping and Taping Transfer Platform (晶圓拆貼一體化轉運台)	Utility Model	Zhuhai Vergiga	ZL202521158524.3	June 5, 2035

As of the Latest Practicable Date, we had applied for registration of the following patents which we consider to be material to our business:

No.	Patent	Patent type	Patentee	Application number	Application date
1	A MOSFET Device with Electrostatic Protection Structure and Preparation Method Thereof (A MOSFET Design Method with Electrostatic Protection Structure) (一種帶靜電保護結構的MOSFET器件及其製備方法(一種帶靜電防護結構的MOSFET設計方法))	Invention Patent	The Company	202410276181.4	March 12, 2024

APPENDIX VI STATUTORY AND GENERAL INFORMATION

No.	Patent	Patent type	Patentee	Application number	Application date
2 . . .	Field-Effect Transistor and Manufacturing Method Thereof (3 A Silicon Carbide MOSFET Device and Manufacturing Method Thereof) (場效應晶體管及其製造方法(3一種碳化矽MOSFET器件及其製造方法))	Invention Patent	The Company	202310618493.4	May 29, 2023
3 . . .	MOSFET and Manufacturing Method Thereof (1 A Silicon Carbide MOSFET Device and Manufacturing Method Thereof) (金氧半場效晶體管及其製造方法(一種碳化矽MOSFET器件及其製造方法))	Invention Patent	The Company	202310614740.3	May 29, 2023
4 . . .	Preparation Method for Fast Recovery Diode (A Preparation Method for Fast Recovery Diode) (快恢復二極管的製備方法(一種快恢復二極管的製造方法))	Invention Patent	The Company	202310133058.2	February 07, 2023
5 . . .	Semiconductor Device (A Power semiconductor Chip Device) (半導體器件(一種功率半導體芯片裝置))	Invention Patent	The Company	202211626871.5	December 16, 2022
6 . . .	Semiconductor Package Structure (A Manufacturing Method of Insulated Gate Bipolar Transistor) (半導體封裝結構(一種絕緣柵雙極型晶體管製作方法))	Invention Patent	The Company	202211715252.3	December 29, 2022
7 . . .	Semiconductor Package Structure (A Manufacturing Method of Insulated Gate Bipolar Transistor) (半導體封裝結構(一種絕緣柵雙極型晶體管製作方法))	Invention Patent	The Company	202211717716.4	December 29, 2022
8 . . .	Diode Device (A High-voltage Diode) (二極管器件(一種高壓二極管))	Invention Patent	The Company	202211652417.7	December 21, 2022

APPENDIX VI STATUTORY AND GENERAL INFORMATION

No.	Patent	Patent type	Patentee	Application number	Application date
9 . . .	Diode Device (A Trench-Type High-voltage Diode) (二極管器件(一種溝槽式的高壓二極管))	Invention Patent	The Company	202211655601.7	December 21, 2022
10 . . .	High-voltage Diode (A High-voltage Diode for EMI Reduction) (高壓二極管(一種降低EMI的高壓二極管))	Invention Patent	The Company	202211652391.6	December 21, 2022
11 . . .	Buried Layer Termination with Deep Trenches and Preparation Method Thereof (Buried Layer Termination Structure with Deep Trenches) (具有深溝槽的埋層終端及其製造方法(一種具有深溝槽的埋層終端結構))	Invention Patent	The Company	202211737562.5	December 29, 2022
12 . . .	Integrated Wafer Transfer Station (Improvement of Quarter Wafer (8K4) Mounting Process) (晶圓拆貼一體化轉運台(四分之一晶圓(8K4)安裝工藝改進))	Utility Model	The Company	202521158524.3	June 06, 2025
13 . . .	A Splash-proof Evaporation Coating Device (A Tungsten Crucible Cover with Nickel Material Splash Prevention Function) (一種防飛濺的蒸鍍裝置(一種具有防止鍍材料飛濺功能的鎢坩堝套))	Utility Model	The Company	202520986725.6	May 19, 2025
14 . . .	Wafer Mounting Mistake-proof Device (Mistake-proof Invention and Improvement of Manual Laminating Machine) (晶圓貼膜防呆裝置(手動貼膜機防呆發明改進))	Utility Model	The Company	202521438554.X	July 09, 2025
15 . . .	A Wafer Auxiliary Ring Management Fixture (Steel Ring Auxiliary Management Fixture) (一種晶圓的輔助環管理治具(鋼環輔助管理治具))	Utility Model	The Company	202521851045X	August 28, 2025

APPENDIX VI STATUTORY AND GENERAL INFORMATION

No.	Patent	Patent type	Patentee	Application number	Application date
16 . . .	A Single Wafer Inspection Fixture (Die Inspection Auxiliary Fixture) (一種單顆晶圓檢測治具(Die檢查輔助治具))	Utility Model	The Company	2025218511912	August 28, 2025
17 . . .	A Turnover Trolley for Semiconductor Auxiliary Materials (An Acid-proof Casing Trolley) (一種用於半導體輔料的周轉推車(一種耐酸城的套箱推車))	Utility Model	The Company	2025219261878	September 08, 2025
18 . . .	A Manual Wafer-Cutting Rotary Fixture (A Manual Wafer-Cutting Rotary Table with Anti-cutting Deviation and Improved Efficiency) (一種用於晶圓的手動切膜旋轉治具(一種具有防切偏且效率提升的手動切膜旋轉台))	Utility Model	The Company	2025219261914	September 08, 2025
19 . . .	A Handle Fixture for Semiconductor Cleaning (A Cleaning Handle Preventing Acid Drips During Pickling Operation) (一種用於半導體清洗的提手治具(一種防止酸洗作業時滴酸的清洗提手))	Utility Model	The Company	2025219557877	September 11, 2025
20 . . .	A Semiconductor Coating Support Fixture (A Ten-claw Steel Ring Enabling Full-surface Conductivity for Vacuum-coated Wafer) (一種用於半導體鍍膜的襯托治具(一種能使真空鍍膜晶圓實現整面導電功能的十爪鋼圈))	Utility Model	The Company	202521997900.8	September 17, 2025
21 . . .	A Splash-proof Special-shaped Evaporation Coating Device for Semiconductor (A Crucible Cover with Splash-proof Function for Evaporation Coating) (一種用於半導體的防飛濺異形蒸鍍裝置(一種具有蒸發鍍膜防飛濺功能的坩堝套))	Utility Model	The Company	2025219557858	September 11, 2025

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No.	Patent	Patent type	Patentee	Application number	Application date
22 . . .	Vertical Double-diffused Semiconductor Power Device (Semiconductor Power Device and Preparation Method Thereof) (垂直雙擴散半導體功率器件(半導體功率器件及其製備方法))	Utility Model	The Company	2025227344904	December 24, 2025

(c) Copyright

As of the Latest Practicable Date, we had registered the following copyright which we consider to be material to our business:

No.	Copyright	Registrant	Registration number	Registration date
1. . .	Vergiga Semiconductor Options System V1.0 (威兆半導體器件選型系統V1.0)	The Company	2019SR1336946	December 11, 2019

(d) Domain Name

As of the Latest Practicable Date, we had registered the following domain name which we consider to be material in relation to our business:

No.	Domain name	Registrant	Expiry date
1. . .	vgsemi.com	The Company	November 11, 2027

Save as aforesaid, as of the Latest Practicable Date, there were no other trademarks, patents or other intellectual or industrial property rights which we consider to be material in relation to our business.

(e) Layout Design of Integrated Circuit

As of the Latest Practicable Date, we had maintained the following layout design of integrated circuits which we consider to be material in relation to our business:

No.	Name	Registrant	Registration number	Expiry date
1. . .	VS8068AD	The Company	BS.195601416	July 18, 2029
2. . .	VS6018BS	The Company	BS.195601424	July 18, 2029
3. . .	VS6410AS	The Company	BS.195601394	July 18, 2029
4. . .	VSD950N70HS	The Company	BS.205525733	April 25, 2030
5. . .	VSE002N03MS-G	The Company	BS.205525741	April 25, 2030
6. . .	VS3508AE	The Company	BS.195601386	July 18, 2029
7. . .	VS6412AE	The Company	BS.195601408	July 18, 2029

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No.	Name	Registrant	Registration number	Expiry date
8. . .	VS6411AS	The Company	BS.205602495	November 15, 2030
9. . .	VSP003N10MS-G	The Company	BS.205532411	May 17, 2030
10. . .	VS12022CAAQ	The Company	BS.205532454	May 17, 2030
11. . .	VS0009N06MS-G	The Company	BS.20553242X	May 17, 2030
12. . .	VS6614GS	The Company	BS.205605842	November 22, 2030
13. . .	VS4110AT	The Company	BS.205605834	November 22, 2030
14. . .	VS150N08BT	The Company	BS.205605710	November 22, 2030
15. . .	VSI008N10MS3-K	The Company	BS.205602509	November 15, 2030
16. . .	VS3618BE	The Company	BS.205605826	November 22, 2030
17. . .	VS3510AE	The Company	BS.205602479	November 15, 2030
18. . .	VSP004N10MS-G	The Company	BS.20560580X	November 22, 2030
19. . .	VSI008N10MS3	The Company	BS.205602487	November 15, 2030
20. . .	VS1606GS	The Company	BS.205605818	November 22, 2030
21. . .	DMOS Power Chip VS6613GS (DMOS功率 芯片VS6613GS)	The Company	BS.215589955	July 26, 2031
22. . .	DMOS Power Chip VS4410AT (DMOS功率 芯片VS4410AT)	The Company	BS.215601467	August 17, 2031
23. . .	DMOS Power Chip VST006N15HS-G (DMOS功率芯片 VST006N15HS-G)	The Company	BS.215601351	August 17, 2031
24. . .	DMOS Power Chip VS12021CA6Q (DMOS 功率芯片VS12021CA6Q)	The Company	BS.215589785	July 26, 2031
25. . .	DMOS Power Chip VS12040CA6Q (DMOS 功率芯片VS12040CA6Q)	The Company	BS.21558984X	July 26, 2031
26. . .	DMOS Power Chip VS12015CAAQ (DMOS 功率芯片VS12015CAAQ)	The Company	BS.215589696	July 26, 2031
27. . .	DMOS Power Chip VS12010CACQ (DMOS 功率芯片VS12010CACQ)	The Company	BS.215589688	July 26, 2031
28. . .	DMOS Power Chip VS20270CA4Q (DMOS 功率芯片VS20270CA4Q)	The Company	BS.215589890	July 26, 2031
29. . .	DMOS Power Chip VS4401ATH (DMOS功率 芯片VS4401ATH)	The Company	BS.215601408	August 17, 2031

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No.	Name	Registrant	Registration number	Expiry date
30.	DMOS Power Chip VS8402AMH (DMOS功率芯片VS8402AMH)	The Company	BS.215601491	August 17, 2031
31.	DMOS Power Chip VSE007N04MS-G (DMOS功率芯片VSE007N04MS-G)	The Company	BS.215601424	August 17, 2031
32.	DMOS Power Chip VSE009NE6MS-G (DMOS功率芯片VSE009NE6MS-G)	The Company	BS.215601475	August 17, 2031
33.	DMOS Power Chip VSP009N15HS-G (DMOS功率芯片VSP009N15HS-G)	The Company	BS.215601440	August 17, 2031
34.	DMOS Power Chip VS1605APM (DMOS功率芯片VS1605APM)	The Company	BS.215601335	August 17, 2031
35.	DMOS Power Chip VST085N65HS (DMOS功率芯片VST085N65HS)	The Company	BS.215608100	August 26, 2031
36.	DMOS Power Chip VSP003N10HS-G (DMOS功率芯片VSP003N10HS-G)	The Company	BS.215601432	August 17, 2031
37.	DMOS Power Chip VS6616GS (DMOS功率芯片VS6616GS)	The Company	BS.215589963	July 26, 2031
38.	DMOS Power Chip VS20031CA6Q (DMOS功率芯片VS20031CA6Q)	The Company	BS.215589971	July 26, 2031
39.	DMOS Power Chip VS20100CA4Q (DMOS功率芯片VS20100CA4Q)	The Company	BS.21558998X	July 26, 2031
40.	DMOS Power Chip VSP004N10MS-K (DMOS功率芯片VSP004N10MS-K)	The Company	BS.215589998	July 26, 2031
41.	DMOS Power Chip VST012N12MS-G (DMOS功率芯片VST012N12MS-G)	The Company	BS.215608119	August 26, 2031
42.	DMOS Power Chip VS40200AT (DMOS功率芯片VS40200AT)	The Company	BS.215608097	August 26, 2031
43.	DMOS Power Chip VSP007N12MS-G (DMOS功率芯片VSP007N12MS-G)	The Company	BS.215608127	August 26, 2031

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No.	Name	Registrant	Registration number	Expiry date
44.	DMOS Power Chip VS3615GE (DMOS功率芯片VS3615GE)	The Company	BS.215601394	August 17, 2031
45.	FRD Power Chip HCDD5F65H1 (FRD功率芯片HCDD5F65H1)	The Company	BS.225620995	November 27, 2032
46.	FRD Power Chip HCDW20F120S1 (FRD功率芯片HCDW20F120S1)	The Company	BS.225621002	November 27, 2032
47.	FRD Power Chip HCDW40F65H1 (FRD功率芯片HCDW40F65H1)	The Company	BS.225620936	November 27, 2032
48.	FRD Power Chip HCDW40F120S1 (FRD功率芯片HCDW40F120S1)	The Company	BS.225621029	November 27, 2032
49.	FRD Power Chip HCDW75F120S1 (FRD功率芯片HCDW75F120S1)	The Company	BS.225621037	November 27, 2032
50.	IGBT Power Chip HCFF150R12KAH1 (IGBT功率芯片HCFF150R12KAH1)	The Company	BS.225620960	November 27, 2032
51.	IGBT功率芯片 HCKD5N65AM2	The Company	BS.225621053	November 27, 2032
52.	IGBT Power Chip HCKW25N120H2 (IGBT功率芯片HCKW25N120H2)	The Company	BS.225621061	November 27, 2032
53.	IGBT Power Chip HCKW40N120CS2 (IGBT功率芯片HCKW40N120CS2)	The Company	BS.22562107X	November 27, 2032
54.	IGBT Power Chip IGBT功率芯片HCKW40N120H1	The Company	BS.225620987	November 27, 2032
55.	IGBT Power Chip HCKW60N65BH2A (IGBT功率芯片HCKW60N65BH2A)	The Company	BS.225622874	December 1, 2032
56.	IGBT Power Chip HCKW75N65BH2 (IGBT功率芯片HCKW75N65BH2)	The Company	BS.225622866	December 1, 2032
57.	SGT Power Chip SGT功率芯片VS3603GPMT	The Company	BS.225622815	December 1, 2032
58.	SGT Power Chip VS3620GEMC (SGT功率芯片VS3620GEMC)	The Company	BS.225622807	December 1, 2032
59.	SGT Power Chip VS4833GE (SGT功率芯片VS4833GE)	The Company	BS.225622858	December 1, 2032

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No.	Name	Registrant	Registration number	Expiry date
60.	SGT Power Chip VS8802GPHT (SGT功率芯片VS8802GPHT)	The Company	BS.225622823	December 1, 2032
61.	SGT Power Chip VSP002N03MST-G (SGT功率芯片VSP002N03MST-G)	The Company	BS.22562284X	December 1, 2032
62.	DMOS Power Chip VSU60R030HS-F (DMOS功率芯片VSU60R030HS-F)	The Company	BS.225625970	December 11, 2032
63.	DMOS Power Chip VSU040N65HS-F (DMOS功率芯片VSU040N65HS-F)	The Company	BS.225625962	December 11, 2032
64.	T-DMOS Power Device Chip VSP003N06MS-G (T-DMOS功率器件芯片VSP003N06MS-G)	The Company	BS.225625938	December 11, 2032
65.	SGT MOS Power Device Chip VS30025CACQ (SGT MOS功率器件芯片VS30025CACQ)	The Company	BS.225625989	December 11, 2032
66.	T-DMOS Power Device Chip T-DMOS功率器件芯片VS24170CA4Q	The Company	BS.225625954	December 11, 2032
67.	T-DMOS Power Device Chip VS24025CAAQ (T-DMOS功率器件芯片VS24025CAAQ)	The Company	BS.225625997	December 11, 2032
68.	T-DMOS Power Device Chip T-DMOS功率器件芯片VS6832DS-AG	The Company	BS.225625946	December 11, 2032
69.	T-DMOS Power Device Chip VS4602AP (T-DMOS功率器件芯片VS4602AP)	The Company	BS.225625903	December 11, 2032
70.	T-DMOS Power Chip VS24015CACQ (T-DMOS功率芯片VS24015CACQ)	The Company	BS.225628112	December 15, 2032
71.	T-DMOS Power Device Chip VST015N15HS-G (T-DMOS功率器件芯片VST015N15HS-G)	The Company	BS.22562804X	December 15, 2032
72.	T-DMOS Power Device Chip VSM008N15HS-G (T-DMOS功率器件芯片VSM008N15HS-G)	The Company	BS.225628066	December 15, 2032

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No.	Name	Registrant	Registration number	Expiry date
73.	T-DMOS Power Device Chip VSM004N15HS-G (T-DMOS功率器件芯片 VSM004N15HS-G)	The Company	BS.225628090	December 15, 2032
74.	T-DMOS Power Device Chip VS24080CA6Q (T-DMOS功率器件芯片 VS24080CA6Q)	The Company	BS.225628104	December 15, 2032
75.	DMOS Power Chip VS4603DM6 (DMOS功率芯片 VS4603DM6)	The Company	BS.23561498X	December 28, 2033
76.	DMOS Power Chip VS6604GP (DMOS功率芯片 VS6604GP)	The Company	BS.235614998	December 28, 2033
77.	DMOS Power Chip VSO009N06MS-GA (DMOS功率芯片 VSO009N06MS-GA)	The Company	BS.235615005	December 28, 2033
78.	DMOS Power Chip VSP004N10MSC-G (DMOS功率芯片 VSP004N10MSC-G)	The Company	BS.235615013	December 28, 2033
79.	DMOS Power Chip VSP007P06MS (DMOS功率芯片 VSP007P06MS)	The Company	BS.235614971	December 28, 2033
80.	DMOS Power Chip DMOS功率芯片 VSU040N65HS3	The Company	BS.235614955	December 28, 2033
81.	SGT MOS Power Chip VS1891GKH (SGT MOS功率芯片 VS1891GKH)	The Company	BS.235614963	December 28, 2033
82.	Trench DMOS Power Chip VS3618AP (Trench MOS功率芯片 VS3618AP)	The Company	BS.245502815	January 14, 2034
83.	SGT MOS Power Chip VS1891GMH (SGT MOS功率芯片 VS1891GMH)	The Company	BS.245607242	December 30, 2034
84.	Trench MOS Power Chip VS3518AE (Trench MOS功率芯片 VS3518AE)	The Company	BS.245607331	December 30, 2034
85.	Trench MOS Power Chip VS3618AE (Trench MOS功率芯片 VS3618AE)	The Company	BS.245607218	December 30, 2034
86.	Trench MOS Power Chip VS3622DE (Trench MOS功率芯片 VS3622DE)	The Company	BS.24560734X	December 30, 2034
87.	Trench MOS Power Chip VS3698AP (Trench MOS功率芯片 VS3698AP)	The Company	BS.245607234	December 30, 2034

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No.	Name	Registrant	Registration number	Expiry date
88. .	SGT MOS Power Chip VS4620GEMC (SGT MOS功率芯片 VS4620GEMC)	The Company	BS.245607250	December 30, 2034
89. .	SGT MOS Power Chip VS4802GPHT (SGT MOS功率芯片 VS4802GPHT)	The Company	BS.245607277	December 30, 2034
90. .	DMOS Power Chip VS3610AE (DMOS功率 芯片 VS3610AE)	The Company	BS.245607293	December 30, 2034
91. .	DMOS Power Chip VS6614DS (DMOS功率 芯片 VS6614DS)	The Company	BS.245607285	December 30, 2034
92. .	DMOS Power Chip VS6614GE (DMOS功率 芯片 VS6614GE)	The Company	BS.245607307	December 30, 2034
93. .	DMOS Power Chip VS40200AP (DMOS功率 芯片 VS40200AP)	The Company	BS.245607358	December 30, 2034
94. .	DMOS Power Chip VSD011N10HS-G (DMOS功率芯片 VSD011N10HS-G)	The Company	BS.245607323	December 30, 2034
95. .	DMOS Power Chip VSP003N08HS-GA (DMOS功率芯片 VSP003N08HS-GA)	The Company	BS.245607366	December 30, 2034
96. .	DMOS Power Chip VSD007P06MS (DMOS功率芯片 VSD007P06MS)	The Company	BS.245607374	December 30, 2034
97. .	Chip Scale Package DMOS chip VS12022CZAQ (芯片級封裝DMOS芯片 VS12022CZAQ)	Zhuhai Vergiga	BS.25553700X	May 20, 2035
98. .	Chip Scale Package DMOS chip VS12040CZ6Q (芯片級封裝DMOS芯片 VS12040CZ6Q)	Zhuhai Vergiga	BS.255536984	May 20, 2035
99. .	Chip Scale Package DMOS chip VS20100CZ4Q (芯片級封裝DMOS芯片 VS20100CZ4Q)	Zhuhai Vergiga	BS.255536992	May 20, 2035
100. .	VGIG55A0 Chip (芯片VGIG55A0)	The Company	BS.255596995	December 1, 2035
101. .	VGIG55B0 Chip (芯片VGIG55B0)	The Company	BS.255597002	December 1, 2035

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No.	Name	Registrant	Registration number	Expiry date
102 .	SGT MOS Power Chip VS4653GPHT (SGT MOS功率芯片 VS4653GPHT)	The Company	BS.255604602	December 24, 2035
103 .	SGT MOS Power Chip VS8801GKH (SGT MOS 功率芯片VS8801GKH)	The Company	BS.255604610	December 24, 2035
104 .	Trench MOS Power Chip VSE2R5N03MS (Trench MOS功率芯片 VSE2R5N03MS)	The Company	BS.255604629	December 24, 2035
105 .	SGT MOS Power Chip QH4007GPHT (SGT MOS功率芯片 QH4007GPHT)	The Company	BS.255604580	December 24, 2035
106 .	DMOS Power Chip VSP001N06HST-G (DMOS功率芯片 VSP001N06HST-G)	The Company	BS.255604637	December 24, 2035

C. FURTHER INFORMATION ABOUT OUR DIRECTORS AND SUBSTANTIAL SHAREHOLDERS

1. Disclosure of Interests

(a) *Interests of our Directors and chief executive*

Immediately following the completion of the [REDACTED] (assuming the [REDACTED] is not exercised), the interests or short positions of our Directors and chief executive in the shares, underlying shares and debentures of our Company or our associated corporations (within the meaning of Part XV of the SFO) which will have to be notified to our Company and the Stock Exchange pursuant to Divisions 7 and 8 of Part XV of the SFO (including interests or short positions which they are taken or deemed to have under such provisions of the SFO) or which will be required, pursuant to section 352 of the SFO, to be entered in the register referred to therein, or which will be required, pursuant to the Model Code for Securities Transactions by Directors of Listed Issuers as set out in Appendix C3 to the Listing Rules, to be notified to our Company and the Stock Exchange, once the H Shares are [REDACTED], are set out below:

(i) *Interest in our Company*

Name of Shareholder	Nature of interest ⁽¹⁾	Number and class of Shares or underlying Shares held	Shareholding in relevant class of Shares or underlying Shares held as of the Latest Practicable Date	Approximate shareholding in relevant class of Shares after the [REDACTED] ⁽²⁾
Mr. Li.	Beneficial owner	24,251,965 Shares	39.19%	[REDACTED]%

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Name of Shareholder	Nature of interest ⁽¹⁾	Number and class of Shares or underlying Shares held	Shareholding in relevant class of Shares or underlying Shares held as of the Latest Practicable Date	Approximate shareholding in relevant class of Shares after the [REDACTED] ⁽²⁾
	Interest in controlled corporation ⁽³⁾	13,979,487 Shares	22.59%	[REDACTED]%

Notes:

- (1) All interests stated are long positions.
- (2) The calculation is based on the total number of [REDACTED] Shares in issue immediately following the completion of the [REDACTED] (assuming the [REDACTED] is not exercised).
- (3) As of the Latest Practicable Date, Zhoushan Tuowei was held as to 88% by Mr. Li as its general partner and 12% by Ms. Wu Shaodan (吳少丹), Mr. Li’s spouse. Zhoushan Jicheng was held as to approximately 90.15% by Mr. Li as its general partner and approximately 9.85% by 35 limited partners, each of whom is our current employee and an Independent Third Party holding less than 10% of partnership interest of Zhoushan Jicheng. By virtue of the SFO, Mr. Li is deemed to be interested in the Shares held by Zhoushan Tuowei and Zhoushan Jicheng. For details, see “History, Development and Corporate Structure — Corporate Structure” and “Substantial Shareholders” in this document.

(ii) Interest in our associated corporations

So far as our Directors are aware, immediately following the completion of the [REDACTED], no Directors or the chief executive will, directly or indirectly, be interested in the shares or underlying shares of the associated corporations of our Company.

(b) Interests of our substantial Shareholders

Save as disclosed in the section headed “Substantial Shareholders” in this document, immediately following the completion of the [REDACTED] and the Conversion of Unlisted Shares into H Shares, our Directors are not aware of any other person (other than our Directors or chief executive) who will have an interest or short position in our Shares or the underlying Shares which would fall to be disclosed to us and the Stock Exchange under the provisions of Divisions 2 and 3 of Part XV of the SFO, or who is, directly or indirectly, interested in 10% or more of the issued voting shares of our Company or any other members of our Group.

2. Directors’ Service Contracts and Letters of Appointment

Each of our executive Directors entered into a service contract with our Company on [●]. The terms of appointment under the service contracts are for an initial term of three years from the [REDACTED], subject to termination in accordance with their respective terms. The service contracts may be renewed in accordance with our Articles of Association and the applicable Listing Rules.

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We issued letters of appointment to each of our independent non-executive Directors on [●]. The terms of appointment under the letters of appointment are for an initial term of three years from the [REDACTED], subject to termination in accordance with their respective terms. The letters of appointment may be renewed in accordance with our Articles of Association and the applicable Listing Rules.

Save as disclosed above, none of our Directors have entered, or have proposed to enter, a service contract with any member of our Group (other than contracts expiring or determinable by the employer within one year without the payment of compensation (other than statutory compensation)).

3. Directors’ Remuneration

The aggregate remuneration paid and benefits in kind granted to our Directors by our Group in respect of the last completed financial year, being year ended December 31, 2025, was RMB5.8 million. For details of our Directors’ emoluments during the Track Record Period, see Note 9 to the Accountants’ Report in Appendix I to this document.

Under the arrangements in force at the date of this document, we estimate the aggregate remuneration payable to, and benefits in kind receivable by, our Directors by our Group in respect of the year ending December 31, 2026 to be approximately RMB5.9 million.

D. PRE-[REDACTED] EQUITY INCENTIVE PLAN

Purpose

The main purpose of the Pre-[REDACTED] Equity Incentive Plan is to improve the incentive mechanism of the Group, further enhance the work enthusiasm and creativity of the participants of our employees, promote the continued growth of the performance of the Group, and bring economic benefits to the eligible participants under the Pre-[REDACTED] Equity Incentive Plan while enhancing the value of the Group, so as to realize the common development of the eligible participants under the Pre-[REDACTED] Equity Incentive Plan and the Group.

Administration

The Shareholders’ meeting is the highest decision-making body of the Pre-[REDACTED] Equity Incentive Plan and is responsible for reviewing and approving its formulation, modification, and termination. As approved by the Shareholders, the Board is responsible for the day-to-day management, implementation, interpretation and amendment of the Pre-[REDACTED] Equity Incentive Plan.

Eligible Participants

The eligible participants under the Pre-[REDACTED] Equity Incentive Plan include our Group’s key personnel, other employees, and other participants as determined by the Board necessary to be awarded.

Form of Awards under the Pre-[REDACTED] Equity Incentive Plan

The participants shall subscribe for partnership interests of the ESOP Platforms as limited partners according to the number of awards granted under the Pre-[REDACTED] Equity Incentive Plan, thereby indirectly holding the Shares of our Company by virtue of their capacity as limited partners of the relevant ESOP Platforms.

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Lock-up Period and Transfer Restrictions

Awards granted under the Pre-[REDACTED] Equity Incentive Plan will be subject to a lock-up period from the date of grant ending upon the expiry date of the statutory lock-up period from the date of successful [REDACTED] of the Company on the Hong Kong Stock Exchange (the “**First Lock-up Period**”). During the First Lock-up Period, without the written consent from the Board, the grantees shall not directly or indirectly dispose the partnership interests held in the ESOP Platforms.

Upon the expiry of the First Lock-up Period, the restricted Shares will be unlocked in tranches of 25%, 25% and 50% in each of the three unlocking periods that occur between the first [REDACTED] date after the First Lock-up Period and the last [REDACTED] day up to 24 months (the “**Second Lock-up Period**”), respectively. During the Second Lock-up Period, the grantee may transfer all of his/her partnership interests if the Shares underlying the corresponding partnership interests are less than 100.

Rights Attached to Awards

The general partners of the ESOP Platforms shall exercise voting rights on behalf of the eligible participants under the Pre-[REDACTED] Equity Incentive Plan in respect of the Shares underlying the awards. The eligible participants under the Pre-[REDACTED] Equity Incentive Plan have the rights to any dividends or distributions from any Shares underlying the awards.

Details of Shares held by the ESOP Platforms and interests granted under the Pre-[REDACTED] Equity Incentive Plan

As of the Latest Practicable Date, all partnership interests in the ESOP Platforms have been granted to, vested in and subscribed by the partners, and the relevant registration had been completed. The ESOP Platforms held a total of 8,083,988 Shares in our Company, representing approximately 13.06% of the total issued shares of our Company immediately prior to the [REDACTED].

As of the Latest Practicable Date, the partnership interest in the relevant ESOP Platforms held by Directors, senior management and connected persons under the Pre-[REDACTED] Equity Incentive Plan are set out below:

Percentage of partnership interest in relevant ESOP Platforms		
Name	Zhoushan Jicheng	Weizhuyexin
<i>Directors and senior management of the Company</i>		
Mr. LI Weicon (李偉聰)	90.15%	6.99%
Mr. HUANG Yi (黃義)	—	10.14%
Mr. HE Wei (何偉)	—	9.73%
Mr. JIANG Chunliang (姜春亮)	—	7.30%
Mr. SHI Shuai (史帥)	8.33%	5.84%
Ms. XU Caifang (徐采芳)	—	4.87%
<i>Connected person of the Company (other than the Directors as listed above)</i>		
Mr. ZHANG Xiaoqing (張小青) ⁽¹⁾	—	2.43%
<i>Other grantees</i>		
—	1.52%	52.70% ⁽²⁾

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Notes:

- (1) Mr. ZHANG Xiaoqing (張小青) is the chief executive of our principal subsidiaries.
- (2) None of the grantees holds more than 30% of its partnership interests therein.

E. OTHER INFORMATION

1. Estate Duty

Our Directors have been advised that no material liability for estate duty would be likely to fall upon any member of our Group.

2. Litigation

Save as disclosed in this document and so far as our Directors are aware, no litigation or claim of material importance is pending or threatened against any member of our Group.

3. Sole Sponsor

The Sole Sponsor has made an [REDACTED] on our behalf to the [REDACTED] Committee for the [REDACTED] of, and permission to [REDACTED] in, the H Shares in issue and to be issued pursuant to the [REDACTED] (including any additional H Shares which may be issued pursuant to the exercise of the [REDACTED]).

The Sole Sponsor satisfies the independence criteria applicable to sponsors set out in Rule 3A.07 of the Listing Rules. The Sole Sponsor will receive a fee of US\$1,150,000 for acting as a sponsor for the [REDACTED].

4. No Material Adverse Change

Save as disclosed in this document, our Directors confirm that there has been no material adverse change in the financial or trading position of our Group since May 31, 2026 (being the date to which the latest consolidated financial statements of our Group were prepared).

5. Qualification and Consent of Experts

This document contains statements made by the following experts:

Name	Qualification
GF Capital (Hong Kong) Limited	A licenced corporation to conduct Type 6 (advising on corporate finance) regulated activity as defined under the SFO
Global Law Office.	Legal advisor as to PRC laws
Ernst & Young.	Certified public accountants and public interest entity auditor
China Insights Industry Consultancy Limited . . .	Independent industry consultant
Hogan Lovells Cadwalader International LLP	Legal advisor to U.S. Foreign Investment and International Sanctions laws

As of the Latest Practicable Date, none of the experts named above had any shareholding in any member of our Group or the right (whether legally enforceable or not) to subscribe for or to nominate persons to subscribe for securities in any member of our Group.

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The experts named above have each given and have not withdrawn their respective written consents to the issue of this document with copies of their reports, letters, opinions or summaries of opinions (as the case maybe) and references to their names included in the form and context in which they are respectively included.

6. Promoters

Information of our promoters at the time of our Company’s conversion into a joint stock limited company on June 28, 2022 is as follows:

Shareholder	Number of Shares held upon our conversion	Percentage shareholding
Mr. Li	10,000,000	44.18%
Zhoushan Tuowei	3,333,334	14.73%
Zhoushan Jicheng	2,430,936	10.74%
OPPO Guangdong	1,289,168	5.70%
Weizhuyexin	902,397	3.99%
Fenhu Qinhe VC	838,169	3.70%
Yuanhe Puhua	705,985	3.12%
Intel	679,056	3.00%
Yancheng VC	669,819	2.96%
Hubei Xiaomi	615,732	2.72%
Moqin Intelligent.	541,255	2.39%
Fenglin VC	394,011	1.74%
Fengyuan VC	235,328	1.04%
Total	22,635,190	100.00%

Save as disclosed in this document, within the two years immediately preceding the date of this document, no cash, securities or other benefit has been paid, allotted or given nor are any proposed to be paid, allotted or given to the above promoters in connection with the [REDACTED] and the related transactions described in this document.

7. Preliminary Expenses

We have not incurred any material preliminary expenses.

8. Binding Effect

This document shall have the effect, where an application is made in pursuance hereof, of rendering all persons concerned bound by all of the provisions (other than the penal provisions) of sections 44A and 44B of the Companies (Winding Up and Miscellaneous Provisions) Ordinance insofar as applicable.

9. Bilingual Document

The English language and Chinese language versions of this document are being published separately in reliance upon the exemption provided by section 4 of the Companies (Exemption of Companies and Prospectuses from Compliance with Provisions) Notice (Chapter 32L of the Laws of Hong Kong).

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10. Miscellaneous

- (a) Save as disclosed in this document, within the two years immediately preceding the date of this document:
 - (i) no commissions, discounts, brokerages or other special terms have been granted in connection with the issue or sale of any capital of any member of our Group, and no Directors, promoters or experts named in “— E. Other Information — 5. Qualification and Consent of Experts” in this section have received any such payment or benefit;
 - (ii) no capital of any member of our Group has been issued or is proposed to be issued for cash or issued as fully or partly paid up otherwise than in cash;
 - (iii) none of our Directors or the experts named in “— E. Other Information — 5. Qualification and Consent of Experts” in this section have any interest, direct or indirect, in the promotion of, or in any assets which have been, acquired or disposed of by or leased to, any member of our Group, or are proposed to be acquired or disposed of by or leased to any member of our Group; and
 - (iv) no commissions (but not including commissions to [REDACTED]) have been paid or payable for subscribing or agreeing to subscribe, or procuring or agreeing to procure subscriptions, for any Shares or debentures of our Company.
- (b) Save as disclosed in this document:
 - (i) there is no arrangement under which future dividends are waived or agreed to be waived;
 - (ii) our Company has no outstanding convertible debt securities or debentures;
 - (iii) there are no founder, management or deferred shares in our Company or any of our subsidiaries;
 - (iv) no capital of any member of our Group is under option, or is agreed conditionally or unconditionally to be put under option;
 - (v) there has not been any interruption in the business of our Group which may have or have had a significant effect on our financial position in the 12 months immediately preceding the date of this document; and
 - (vi) none of our Directors are materially interested in any contract or arrangement subsisting at the date of this document which is significant in relation to the business of our Group.